

# MMBV105G

CASE 318-02/03, STYLE 8  
SOT-23 (TO-236AA/AB)

## VOLTAGE VARIABLE CAPACITANCE DIODE

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	Vdc
Forward Current	$I_F$	200	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	350 2.8	mW mW/ $^\circ\text{C}$
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$
*Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$

\*Package mounted on 99.5% alumina 10 x 8 x 0.6 mm.

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Reverse Breakdown Voltage ( $I_R = 10 \mu\text{Adc}$ )	$V_{(BR)}$	30	—	—	Vdc
Reverse Voltage Leakage Current ( $V_R = 28 \text{ Vdc}$ )	$I_R$	—	—	50	nAdc
Series Inductance (f = 250 MHz)	$L_S$	—	3.0	—	nH
Diode Capacitance Temperature Coefficient ( $V_R = 3.0 \text{ Vdc}, f = 1.0 \text{ MHz}$ )	$T_{CC}$	—	280	—	ppm/ $^\circ\text{C}$
Diode Capacitance ( $V_R = 25 \text{ Vdc}$ )	$C_T$	1.8	—	2.8	pF
Capacitance ( $V_{R1} = 3.0 \text{ Vdc}, V_{R2} = 25 \text{ Vdc}, f = 1.0 \text{ MHz}$ )	$C_3/C_{25}$	4.0	—	6.0	pF